

**AMENDMENTS TO THE CLAIMS:*****Claims 1-2 (cancelled)***

3. (Previously presented) A semiconductor device to be mounted onto a circuit board, comprising:

    a semiconductor element having a thickness of at most 100 $\mu$ m, said semiconductor element having a first surface bearing a terminal for external connection, and a second surface opposite said first surface;

    a bump on said terminal for external connection;

    a plate confronting said second surface; and

    a bonding layer between said second surface and said plate such that said semiconductor element is bonded to said plate via said bonding layer, said bonding layer having a thickness within a range of from 25 $\mu$ m to 200 $\mu$ m,

    wherein said bonding layer contains filler functioning as a spacer between said semiconductor element and said plate so as to provide said bonding layer with a predetermined thickness.

4. (Previously presented) The semiconductor device according to claim 3, wherein said filler is in contact with said second surface of said semiconductor element and said plate.

5. (Previously presented) The semiconductor device according to claim 3, wherein said filler includes any of inorganic material and polymeric material.

6. (Currently amended) The semiconductor device according to claim + 3, wherein said bonding layer contains filler having at least two different particle sizes, with at least one of said particle sizes being generally equal in dimension to the thickness of said bonding layer.

7. (Currently amended) The semiconductor device according to claim + 3, wherein said bonding layer contains first filler and second filler,

with said first filler having a size generally equal to the thickness of said bonding layer, and said second filler having a particle size distribution in sizes smaller than the size of said first filler.

*Claims 8-11 (cancelled)*

12. (Currently amended) The semiconductor device according to claim ~~1~~ 3, wherein said first surface has a re-wiring layer thereon, with said re-wiring layer having a surface electrode formed on a surface thereof and an internal electrode formed inside thereof, with said internal electrode being in communication with said surface electrode and said terminal for external connection.

*Claims 13-22 (cancelled)*

23. (Previously presented) The semiconductor device according to claim 7, wherein an aggregate percentage of content of said first filler in said bonding layer is at most 30 percent by weight.

24. (Previously presented) The semiconductor device according to claim 7, wherein an aggregate percentage of content of said first filler and said second filler in said bonding layer is at most 30 percent by weight.

25. (Currently amended) The semiconductor device according to claim ~~1~~ 3, wherein said plate has an external shape larger than an external shape of said semiconductor element, and said bonding layer covers a side edge of said semiconductor element.

*Claim 26 (cancelled)*

27. (New) The semiconductor device according to claim 12, further comprising a bump on said surface electrode.